# **Hex Gate**

The MC14572UB hex functional gate is constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. These complementary MOS logic gates find primary use where low power dissipation and/or high noise immunity is desired. The chip contains four inverters, one NOR gate and one NAND gate.

- Diode Protection on All Inputs
- Single Supply Operation
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- NOR Input Pin Adjacent to VSS Pin to Simplify Use As An Inverter
- NAND Input Pin Adjacent to V<sub>DD</sub> Pin to Simplify Use As An Inverter
- NOR Output Pin Adjacent to Inverter Input Pin For OR Application
- NAND Output Pin Adjacent to Inverter Input Pin For AND Application
- Capable of Driving Two Low–power TTL Loads or One Low–Power Schottky TTL Load over the Rated Temperature Range

### MAXIMUM RATINGS (Voltages Referenced to V<sub>SS</sub>) (Note 2.)

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage Range	-0.5 to +18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage Range (DC or Transient)	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient) per Pin	±10	mA
P <sub>D</sub>	Power Dissipation, per Package (Note 3.)	500	mW
T <sub>A</sub>	Ambient Temperature Range	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

- Maximum Ratings are those values beyond which damage to the device may occur.
- Temperature Derating: Plastic "P and D/DW" Packages: – 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.



http://onsemi.com

### MARKING DIAGRAMS



PDIP-16 P SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

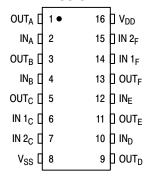
WL, L = Wafer Lot YY, Y = Year WW, W = Work Week

#### **ORDERING INFORMATION**

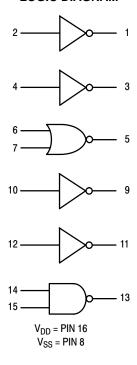
Device	Package	Shipping		
MC14572UBCP	PDIP-16	2000/Box		
MC14572UBD	SOIC-16	48/Rail		
MC14572UBDR2	SOIC-16	2500/Tape & Reel		
MC14572UBF	SOEIAJ-16	See Note 1.		
MC14572UBFEL	SOEIAJ-16	See Note 1.		

 For ordering information on the EIAJ version of the SOIC packages, please contact your local ON Semiconductor representative.

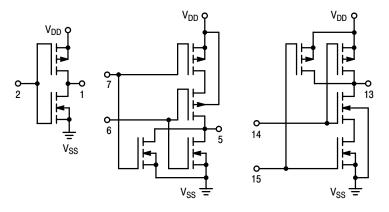
# **PIN ASSIGNMENT**



# LOGIC DIAGRAM



# **CIRCUIT SCHEMATIC**



# **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

			V <sub>DD</sub>	- 5	5°C		25°C		125	5°C	
Characteristic	;	Symbol	Vdc	Min	Max	Min	Тур (4.)	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	V <sub>OL</sub>	5.0 10 15	_ _ _	0.05 0.05 0.05	_ _ _	0 0 0	0.05 0.05 0.05	_ _ _	0.05 0.05 0.05	Vdc
$V_{in} = 0$ or $V_{DD}$	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95	_ _ _	4.95 9.95 14.95	5.0 10 15	_ _ _	4.95 9.95 14.95	_ _ _	Vdc
Input Voltage (V <sub>O</sub> = 4.5 or 0.5 Vdc) (V <sub>O</sub> = 9.0 or 1.0 Vdc) (V <sub>O</sub> = 13.5 or 1.5 Vdc)	"0" Level	V <sub>IL</sub>	5.0 10 15		1.0 2.0 2.5	_ _ _	2.25 4.50 6.75	1.0 2.0 2.5		1.0 2.0 2.5	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V <sub>IH</sub>	5.0 10 15	4.0 8.0 12.5		4.0 8.0 12.5	2.75 5.50 8.25		4.0 8.0 12.5		Vdc
Output Drive Current $ (V_{OH} = 2.5 \text{ Vdc}) $ $ (V_{OH} = 4.6 \text{ Vdc}) $ $ (V_{OH} = 9.5 \text{ Vdc}) $ $ (V_{OH} = 13.5 \text{ Vdc}) $	Source	ІОН	5.0 5.0 10 15	- 1.2 - 0.25 - 0.62 - 1.8	_ _ _ _	- 1.0 - 0.2 - 0.5 - 1.5	- 1.7 - 0.36 - 0.9 - 3.5	_ _ _ _	- 0.7 - 0.14 - 0.35 - 1.1	_ _ _ _	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	_ _ _	0.51 1.3 3.4	0.88 2.25 8.8	_ _ _	0.36 0.9 2.4	_ _ _	mAdc
Input Current		l <sub>in</sub>	15	_	±0.1	_	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	_	_	_	_	5.0	7.5	_	_	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15		0.25 0.5 1.0	_ _ _	0.0005 0.0010 0.0015	0.25 0.5 1.0		7.5 15 30	μAdc
Total Supply Current <sup>(5.)</sup> <sup>(6.)</sup> (Dynamic plus Quiescent, Per Package) (C <sub>L</sub> = 50 pF on all outputs, all buffers switching)		l <sub>T</sub>	5.0 10 15			$I_{T} = (3$	.89 μA/kHz) .80 μA/kHz) .68 μA/kHz)	f + I <sub>DD</sub>	•		μAdc

<sup>4.</sup> Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
5. The formulas given are for the typical characteristics only at 25°C.
6. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where:  $I_T$  is in  $\mu A$  (per package),  $C_L$  in pF,  $V = (V_{DD} - V_{SS})$  in volts, f in kHz is input frequency, and k = 0.006.

# SWITCHING CHARACTERISTICS (7.) $(C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C})$

Characteristic	Symbol	V <sub>DD</sub>	Min	Typ <sup>(8.)</sup>	Max	Unit
Output Rise Time	t <sub>TLH</sub>					ns
$t_{TLH} = (3.0 \text{ ns/pF}) C_L + 30 \text{ ns}$		5.0	_	180	360	
$t_{TLH} = (1.5 \text{ ns/pF}) C_L + 15 \text{ ns}$		10	_	90	180	
$t_{TLH} = (1.1 \text{ ns/pF}) C_L + 10 \text{ ns}$		15	_	65	130	
Output Fall Time	t <sub>THL</sub>					ns
$t_{THL} = (1.5 \text{ ns/pF}) C_L + 25 \text{ ns}$		5.0	_	100	200	
$t_{THL} = (0.75 \text{ ns/pF}) C_L + 12.5 \text{ ns}$		10	_	50	100	
$t_{THL} = (0.55 \text{ ns/pF}) C_L + 9.5 \text{ ns}$		15	_	40	80	
Propagation Delay Time	t <sub>PLH</sub> ,					ns
$t_{PLH}$ , $t_{PHL} = (1.7 \text{ ns/pF}) C_L + 5 \text{ ns}$	t <sub>PHL</sub>	5.0		90	180	
$t_{PLH}$ , $t_{PHL} = (0.66 \text{ ns/pF}) C_L + 17 \text{ ns}$		10		50	100	
$t_{PLH}$ , $t_{PHL} = (0.5 \text{ ns/pF}) C_L + 15 \text{ ns}$		15		40	80	

- 7. The formulas given are for the typical characteristics only at 25°C.
  8. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

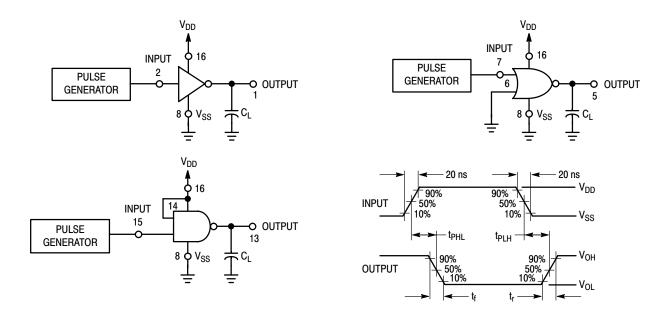
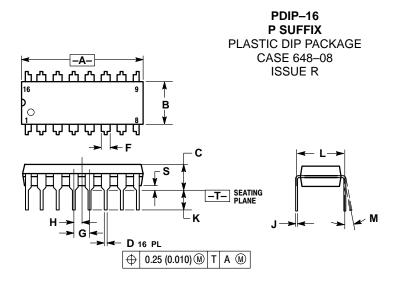


Figure 1. Switching Time Test Circuits and Waveforms

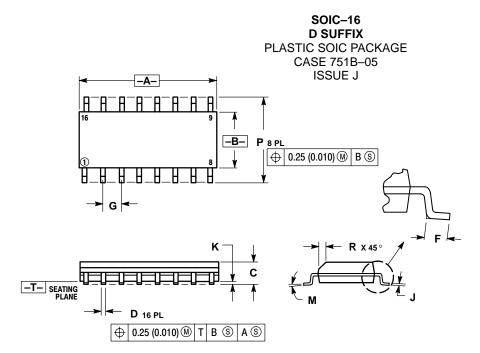
# **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL

	INC	HES	MILLIN	ETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100	BSC	2.54	BSC	
Н	0.050	BSC	1.27	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
M	0°	10°	0°	10 °	
S	0.020	0.040	0.51	1.01	

# **PACKAGE DIMENSIONS**



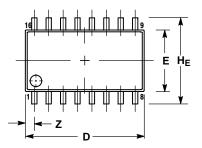
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

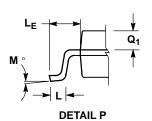
	MILLIN	IETERS	INC	HES	
DIM	MIN	MIN MAX		MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

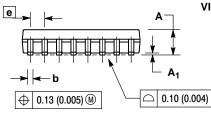
#### **PACKAGE DIMENSIONS**

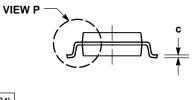
### SOEIAJ-16 **F SUFFIX** PLASTIC EIAJ SOIC PACKAGE CASE 966-01

**ISSUE O** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- 1. DIMENSIONING AND TOLERANGING FEB 2005
  714.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS D AND E DO NOT INCLUDE
  MOLD FLASH OR PROTRUSIONS AND ARE
  MEASURED AT THE PARTING LINE. MOLD FLASH
  OR PROTRUSIONS SHALL NOT EXCEED 0.15
- OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		0.78		0.031

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